F 6 – 25 R 12 KF

T-39-31

EUPEC

Transistor		Transistor		
Elektrische Eigenschaften		Electrical properties		
<u>Höchstzulässige Werte</u> V _{CES}		Maximum rated values 1200	v	
I _C		25	A	
I _{CRM}	$t_p = 1 ms$	50	Α	
P _{tot}	$t_{\rm C} = 25^{\rm o}{\rm C}$	200	W	
V _{GE}		20	۷	
V_{EG}		20	۷	

Charakteristische Werte Characteristic values						
VCE sat	i _{CM} = 25 A,	$v_{GE} = 15 V$,	$t_{vi} = 25^{\circ}C$	typ.	3	V
	і _{см} = 25 А,	v _{GE} = 15 V,	$t_{vj} = 25^{\circ}C$	max.		V
VGE (th)	$v_{CE} = 5 V,$	i _c = 25 mA,	$t_{vj} = 25^{\circ}C$	min.	3	٧
	$v_{CE} = 5 V$,	$i_{\rm C} = 25 {\rm mA},$	$t_{vj} = 25^{\circ}C$	max.	6	V
C _{GE}	$v_{CE} = 10 V$,	$v_{GE} = 0 V$	-			
	f _o = 1 MHz,	$t_{vj} = 25^{\circ}C$		typ.	2,8	nF
i _{CES}	$v_{CE} = 1200 V,$		$t_{vj} = 25^{\circ}C$	typ.	0,2	mΑ
	$v_{CE} = 1200 V$,	$v_{GE} = 0 V,$	$t_{vj} = 125^{\circ}C$	typ.	1	mΑ
i _{GES}	$v_{GE} = 20 V$,	t _{vj} = 25°C		typ.	50	nA
	$v_{GE} = 20 V,$	$t_{vj} = 25^{\circ}C$		max.	500	nA
i _{EGS}	$v_{EG} = 20 V,$	$t_{vj} = 25^{\circ}C$		typ.	50	nA
	$v_{EG} = 20 V,$	$t_{vj} = 25^{\circ}C$		max.	500	nA
t _{on}	i _{CM} = 25 A,	$v_{CE} = 600 V,$				
	$v_{LF} = 15 V$,	$R_G = 51 \Omega$,	$t_{vj} = 25^{\circ}C$	typ.	0,4	μs
	і _{см} = 25 А,	$v_{CE} = 600 \text{ V},$				
	v _{LF} = 15 V,	$R_G = 51 \Omega$,	$t_{vj} = 125^{\circ}C$	typ.	0,5	μs
ts	i _{CM} = 25 A,	$v_{CE} = 600 \text{ V},$				
	v _{LF} = 15 V,	$v_{LR} = 15 V,$				
	$R_G = 51 \Omega$,	$t_{vj} = 25^{\circ}C$		typ.	0,5	μs
	і _{СМ} = 25 А,	$v_{CE} = 600 V,$				
	$v_{LF} = 15 V_{,}$	$v_{LR} = 15 V,$				
	$R_G = 51 \Omega$,	$t_{vj} = 125^{\circ}C$		typ.	0,6	μs
t _f	$i_{CM} = 25 A,$	$v_{CE} = 600 V,$				
	$v_{LF} = 15 V,$	$v_{LR} = 15 V,$				
	$R_G = 51 \Omega$,	$t_{vj} = 25^{\circ}C$		typ.	0,2	μs
	і _{СМ} = 25 А,	$v_{CE} = 600 V,$				
	$v_{LF} = 15 V,$	$v_{LR} = 15 V,$				
	$R_G = 51 \Omega$,	t _{vj} = 125°C		typ.	0,25	μs

<u>Bedingungen für den</u>	Conditions for protection		
Kurzschlußschutz	<u>against short circuits</u>		
$t_{fg} = 10 \ \mu s$,	$V_{\rm CC} = 750 \rm V$,		
$v_{LF} = v_{LR} = 15 V$,	v _{CEM} = 1000 V,		
$R_G = 51 \Omega$,	і _{СМК1} ≈ 250 А,		
$t_{vj} = 125^{\circ}C$,	і _{СМК2} ≈ 200 А		

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Thermische Eigenschaften R _{thJC} DC, pro Baustein / per DC, pro Zweig / per an	•			
t _{vjmax} t _{vjop} t _{stg}	150 ℃ -40 / + 150 ℃ -40 / + 125 ℃			
Inversdiode	Inverse diode			
Elektrische Eigenschaften	Electrical properties			
Höchstzulässige Werte I _{F (max)} I _{FRM} t _p = 1 ms	Maximum rated values 25 A 50 A			

Charakter	istische Werte Characteri	stic valu	es	
VF	$i_F = 25 A, v_{GE} = 0 V, t_{vj} = 25^{\circ}C$	typ.	1,6	v
	$i_F = 25 A, v_{GE} = 0 V, t_{v_i} = 25^{\circ}C$	max.	2,5	v
I _{RM}	$i_{FM} = 25 \text{ A}, -di_F/dt = 100 \text{ A}/\mu \text{s}$			
	$v_{EG} = 10 V, t_{vj} = 25^{\circ}C$	typ.	7	Α
	$i_{FM} = 25 \text{ A}, -di_F/dt = 100 \text{ A}/\mu \text{s}$			
	$v_{EG} = 10 V, t_{vj} = 125^{\circ}C$	typ.	14	Α
Qr	$i_{FM} = 25 \text{ A}, -di_{F}/dt = 100 \text{ A}/\mu \text{s}$			
	$v_{EG} = 10 V, t_{vj} = 25^{\circ}C$	typ.	0,9	μAs
	$i_{FM} = 25 \text{ A}, -di_F/dt = 100 \text{ A}/\mu \text{s}$			
	$v_{EG} = 10 V$, $t_{vj} = 125^{\circ}C$	typ.	3,2	μAs

Thermisch R _{thJC}	e Eigenschaften Thermal propertie DC, pro Baustein / per module DC, pro Zweig / per arm	°C/W °C/W
t _{vjmax} t _{vjop} t _{stg}	-40 / + ⁻ -40 / + ⁻	 သိ သိ

Innere Isolation Isoliermaterial: AIN RMS VISOL

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Insulating material: AIN

Internal insulation

Mechanische Eigenschaften

Mechanical properties

G 690 g M1 3 Nm Μ2 3 Nm

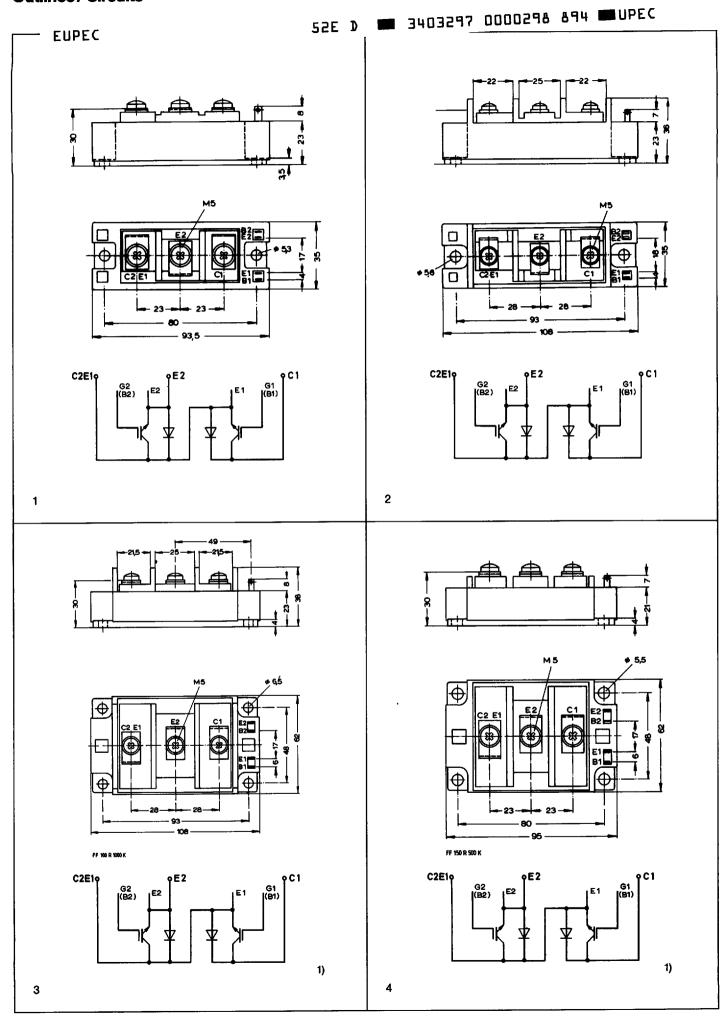
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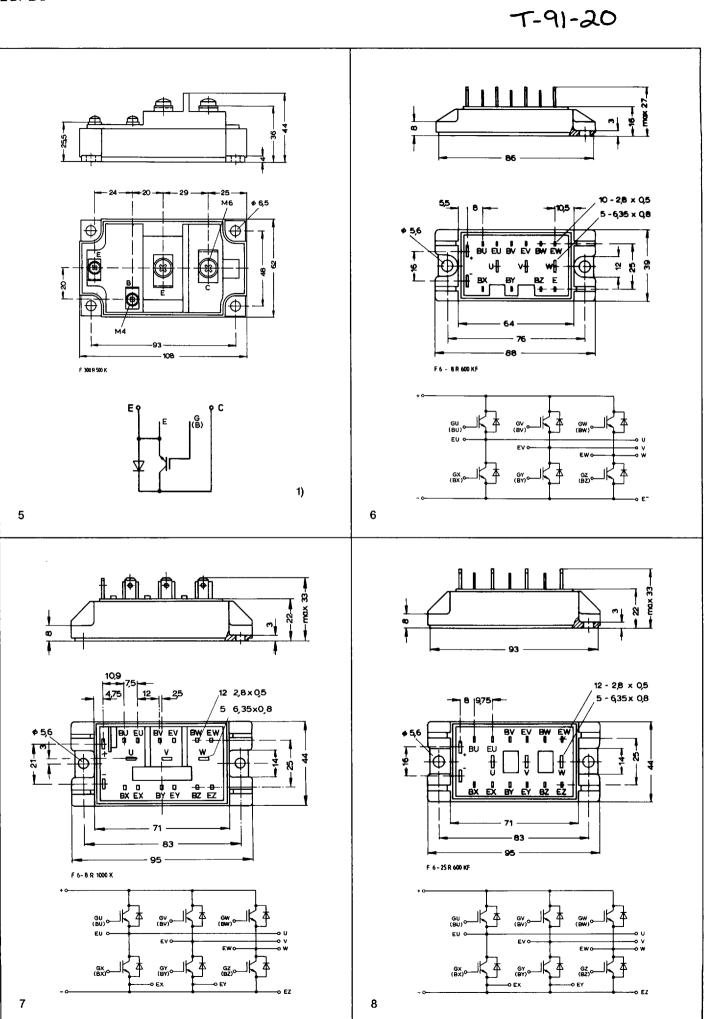
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122



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